

RM8810

Descriptions

N-channel Double MOSFET in a SOT23-6 Plastic Package. It is ESD protested.

Features

advanced trench technology to provide excellent RDS(on), low gate charge.

Applications

Use as Load Switch or PWM application.

Equivalent Circuit



Pinning





2018-06/33 REV:O

Absolute Maximum Ratings(T_a=25°C)

Parameter	Symbol	Rating	Unit		
Drain-Source Voltage	V _{DS}	20	V		
Drain Current - Continuous	I _D (T _a =25℃)	7.0	A		
Drain Current - Continuous	I _D (T _a =70℃)	5.7			
Drain Current – Pulsed	I _{DM}	25	А		
Gate-Source Voltage	V _{GS}	±8.0	V		
Power Dissipation	P _D (T _a =25℃)	1.5	\\/		
Power Dissipation	P _D (T _a =70℃)	1.0	vv		
Junction-to-Ambient ^A	t ≤ 10s	В	83	°C/W	
Junction-to-Ambient ^{AD}	Steady-State	κ _{θJA}	120		
Junction-to-Lead	unction-to-Lead Steady-State		70	°C/W	
Junction and Storage Temperature	T _{j,} T _{stg}	-55 ~ 150	°C		

Electrical Characteristics($T_a=25^{\circ}C$)

Parameter	Symbol	Test Conditions		Min	Тур	Max	Unit	
Drain-Source Breakdown Voltage	BV_{DSS}	V _{GS} =0V	I _D =250μΑ	20			V	
Drain-Source Leakage Current		V _{DS} =16V	V _{GS} =0V			1.0	μA	
Drain-Source Leakage Current	I _{DSS}	V _{DS} =16V Tj=85℃	V _{GS} =0V			10	μA	
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±8V	V _{DS} =0V			±10	μA	
On state drain current	I _{D(ON)}	V _{GS} =4.5V	V _{DS} =5V	25			А	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$	I _D =250μΑ	0.45	0.6	1.0	V	
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =4.5V	I _D =6.0A		16	20		
		V _{GS} =2.5V	I _D =6.0A		19	25	11122	
Forward Transconductance	g fs	V _{DS} =5.0V	I _D =7.0A		50		S	
Forward On Voltage	V _{SD}	V _{GS} =0V	I _S =1.0A			1.3	V	
Maximum Body-Diode Continuous Current	I _S					2	А	
Input Capacitance C _{is}					1295			
Output Capacitance	C _{oss}	V _{DS} =10V f=1.0MHz	V _{GS} =0V		160		pF	
Reverse Transfer Capacitance	C _{rss}				87			

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Electrical Characteristics(T_a=25°C)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Gate resistance	R _g	V _{DS} =0V V _{GS} =0V f=1.0MHz		1.8		KΩ
Total Gate Charge	Qg			10	14	
Gate Source Charge	Q _{gs}	V _{DS} =10V V _{GS} =4.5V		4.2		nC
Gate Drain Charge	Q _{gd}			2.6		
Turn-on Delay Time	t _{d(on)}			280		ns
Rise Time	t _r	V _{DS} =10V V _{GS} =4.5V		328		ns
Turn-off Delay Time	t _{d(off)}	$R_G=3.0\Omega$ $R_L=1.54\Omega$		3.76		μs
Fall Time	t _f			2.24		μs
Body Diode Reverse Recovery Time	t _{rr}	I _F =7A dl/dt=100A/ms V _{GS} =-9V		31		ns
Body Diode Reverse Recovery Charge	Q _{rr}	IF=7A dl/dt=100A/ms V _{GS} =-9V		6.8		nC

Notes:

A. The value of $R_{\theta JA}$ is measured with the device mounted on $1in^2$ FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on $T_{J(MAX)}=150^{\circ}$ C, using ≤ 10 s junction-to-ambient thermal resistance.

C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=150$ °C. Ratings are based on low frequency and duty cycles to keep initial $T_J=25$ °C.

D. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to lead $R_{\theta JL}$ and lead to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300ms pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-ambient thermal impedence which is measured with the device mounted on $1in^2$ FR-4 board with 2oz. Copper, assuming a maximum junction temperature of $T_{J(MAX)}$ =150°C. The SOA curve provides a single pulse rating.





RATING AND CHARACTERISTICS CURVES (RM8810)

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V_{GS} - Q_a 5 1800 V_{DS}=10V I_D=7A 1600 4 1400 C. Capacitance (pF) 1200 V_{GS} (Volts) 1000 800 600 1 400 200 0 0 0 2 4 6 8 10 12 5 0 10 15 20 Q_g (nĈ) V_{DS} (Volts) ID - VDS 10000 100.0 T_{J(Max)}=150° C T_A=25° C 10µs # 1000 11110 10.0 R_{DS(ON)} 100us limited I^D (Ymps) Power (W) -1ms 100 10ms 100ms 1111 10 10s T_{J(Max)}=150° C T_A=25° C 0.1 DC ₩ 1 0.0 0.00001 0.001 0.1 10 1000 0.01 0.1 10 100 1 V_{DS} (Volts) Pulse Width (s) 10 D=Ton/T In descending order D=0.5, 0.3, 0.1, 0.05, 0.02, 0.01, single pulse Z_{6JA} Normalized Transient Thermal Resistance T_{J,PK}=T_A+P_{DM}.Z_{0JA}.R_{0JA} LITH 111111 T I I I III =120° C/W 1 R. ---------0.1 Ħ Po 11111 0.01 Single Pulse t. Ton т 0.001 0.00001 0.0001 0.001 0.01 0.1 10 100 1000 1 Pulse Width (s)

RATING AND CHARACTERISTICS CURVES (RM8810)

Test circuit and waveform



Package Dimensions



Marking Instructions



Note:

8810:	Product Type.
****.	Date code change with manufacturing date.



Temperature Profile for IR Reflow Soldering(Pb-Free)

Notes:

1.Preheating:25~150 °C, Time:60~90sec.

 $2. Peak \qquad Temp.: 245 \pm 5^\circ C, \ Duration: 5 \pm 0.5 sec.$

3. Cooling Speed: 2~10°C/sec.

Resistance to Soldering Heat Test Conditions

Temp:260±5°C Time:10±1 sec

Packaging SPEC.

REEL

Package Type	Units					Dimer	nsion	(unit: mm ³)
i donago ijpo	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
SOT23-5/6	3,000	10	30,000	4	120,000	7″×8	210×205×205	445×230×435



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